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Kind regards,

Team Nexperia

BAV23 series

Dual high-voltage switching diodes Rev. 07 — 19 March 2010

Product data sheet

1. **Product profile**

1.1 General description

Dual high-voltage switching diodes, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration	
NXP JEDEC				
BAV23A	SOT23	TO-236AB	dual common anode	
BAV23C	SOT23	TO-236AB	dual common cathode	
BAV23S	SOT23	TO-236AB	dual series	
BAV23	SOT143B	-	dual isolated	

1.2 Features and benefits

- High switching speed: t_{rr} ≤ 50 ns
- Low leakage current
- Repetitive peak reverse voltage: $V_{RRM} \le 250 \text{ V}$
- Low capacitance: C_d ≤ 2 pF
- Small SMD plastic package

1.3 Applications

- High-speed switching at high voltage
- High-voltage general-purpose switching

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I _R	reverse current	$V_R = 200 \text{ V}$	-	-	100	nA
V_R	reverse voltage		-	-	200	V
t _{rr}	reverse recovery time		<u>[1]</u> -	-	50	ns

^[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.



2. Pinning information

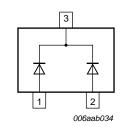
Table 3. Pinning

Table 5.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
BAV23A			
1	cathode (diode 1)		
2	cathode (diode 2)	3	3
3	common anode	1 2	
			006aab099

B VV23C	
DAVZSC	

1	anode (diode 1)
2	anode (diode 2)
3	common cathode

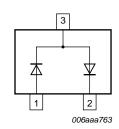




BAV23S

1	anode (diode 1)
2	cathode (diode 2)
3	cathode (diode 1), anode (diode 2)

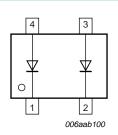




BAV23

1	cathode (diode 1)
2	cathode (diode 2)
3	anode (diode 2)
4	anode (diode 1)





3. Ordering information

Table 4. Ordering information

Type number	Package			
	Name	Description	Version	
BAV23A	-	plastic surface-mounted package; 3 leads	SOT23	
BAV23C				
BAV23S				
BAV23	-	plastic surface-mounted package; 4 leads	SOT143B	

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
BAV23A	*V0
BAV23C	*V9
BAV23S	*V5
BAV23	*L3

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V_{RRM}	repetitive peak reverse voltage		-	250	V
V_R	reverse voltage		-	200	V
I _F	forward current		<u>[1]</u> -	225	mA
			[2] _	125	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM}	non-repetitive peak forward	square wave	[3]		
	current	$t_p = 1 \mu s$	-	9	Α
		$t_p = 100 \ \mu s$	-	3	Α
		$t_p = 10 \text{ ms}$	-	1.7	Α

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

 Table 6.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[4]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Single diode loaded.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	360	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$ unless otherwise specified.

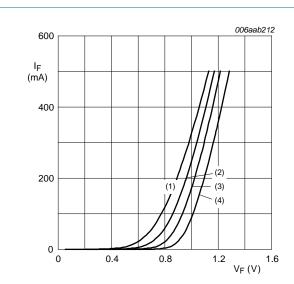
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	Per diode					
V _F	forward voltage	I _F = 100 mA	-	-	1.0	V
		$I_F = 200 \text{ mA}$	-	-	1.25	V
I _R	reverse current	V _R = 200 V	-	-	100	nA
		$V_R = 200 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C_d	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	2	pF
t _{rr}	reverse recovery time		<u>[1]</u> _	-	50	ns

^[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

^[2] Double diode loaded.

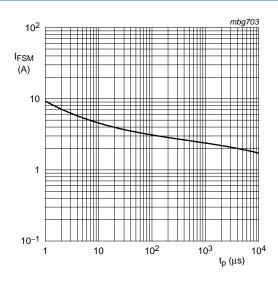
^[3] $T_i = 25$ °C prior to surge.

^[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

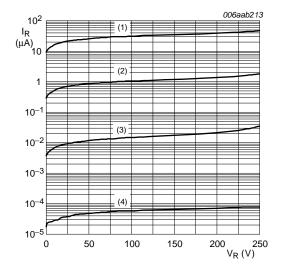
Fig 1. Forward current as a function of forward voltage; typical values



Based on square wave currents.

 $T_j = 25$ °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 3. Reverse current as a function of reverse voltage; typical values

006aab214

200

T_{amb} (°C)

Dual high-voltage switching diodes

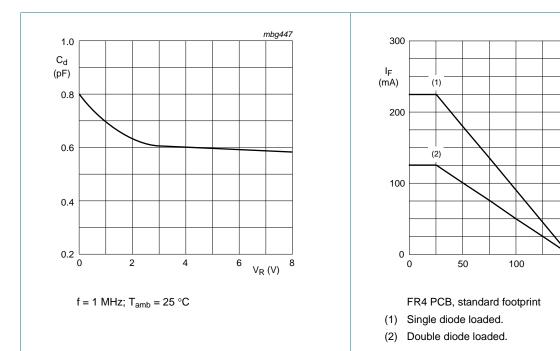
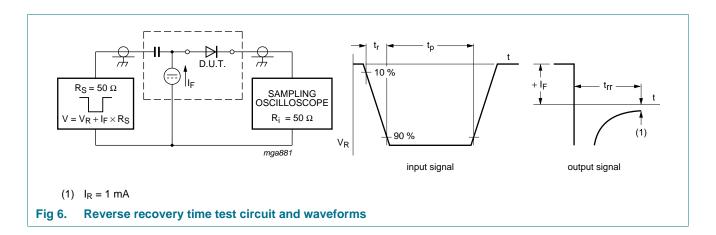


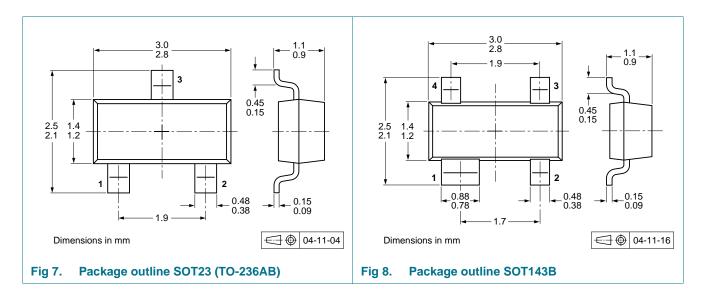
Fig 4. Diode capacitance as a function of reverse voltage; typical values

Fig 5. Forward current as a function of ambient temperature; derating curves

8. Test information



9. Package outline



10. Packing information

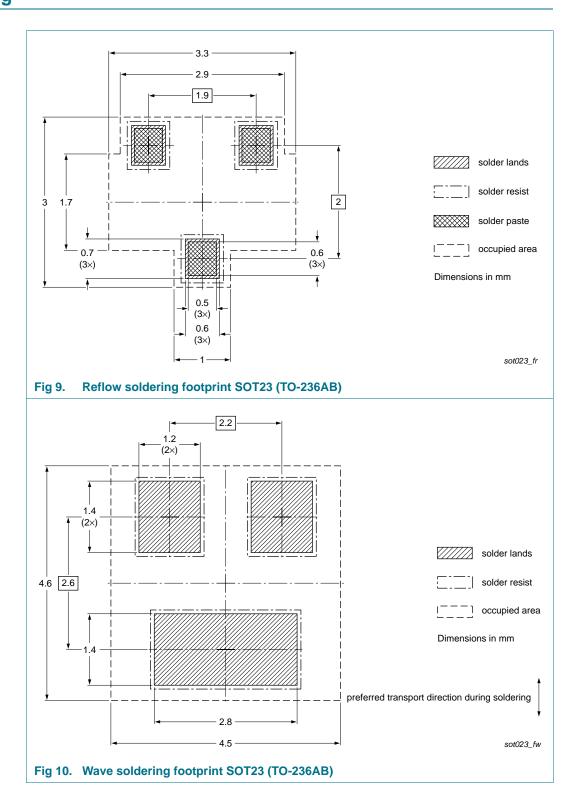
Table 9. Packing methods

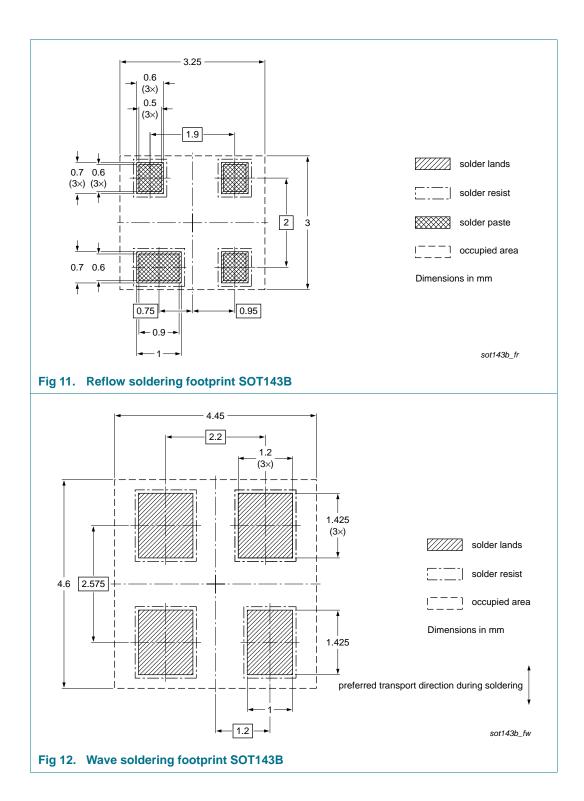
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing o	Packing quantity	
			3000	10000	
BAV23A	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	
BAV23C					
BAV23S					
BAV23	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235	

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering





12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BAV23_SER_7	20100319	Product data sheet	-	BAV23_SER_6		
Modifications:	 Type numbers BAV23A/DG, BAV23C/DG, BAV23S/DG and BAV23/DG deleted 					
	 Type numbers BAV23A and BAV23C added 					
	 <u>Table 5 "Marking codes"</u>: updated 					
	 <u>Figure 6</u>: adaptation of test condition to specified characteristics in <u>Table 8</u> 					
	 <u>Figure 9, 10, 11</u> and <u>12</u>: updated 					
	 Section 13 "Legal information": updated 					
BAV23_SER_6	20080303	Product data sheet	-	BAV23S_5		
				BAV23_2		
BAV23S_5	20011012	Product specification	-	BAV23S_4		
BAV23_2	19960917	Product specification	-	BAV23_1		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BAV23_SER_7

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BAV23 series

Dual high-voltage switching diodes

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